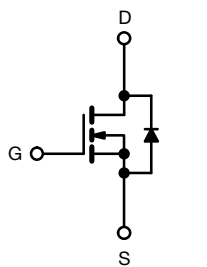
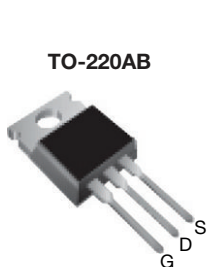


## E Series Power MOSFET



N-Channel MOSFET

### FEATURES

- Low figure-of-merit (FOM):  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Renewable energy
  - Solar (PV inverters)

### PRODUCT SUMMARY

|                                         |                 |       |
|-----------------------------------------|-----------------|-------|
| $V_{DS}$ (V) at $T_J$ max.              | 650             |       |
| $R_{DS(on)}$ max. ( $\Omega$ ) at 25 °C | $V_{GS} = 10$ V | 0.099 |
| $Q_g$ max. (nC)                         | 150             |       |
| $Q_{gs}$ (nC)                           | 24              |       |
| $Q_{gd}$ (nC)                           | 42              |       |
| Configuration                           | Single          |       |

### ORDERING INFORMATION

|                                 |                |
|---------------------------------|----------------|
| Package                         | TO-220AB       |
| Lead (Pb)-free                  | SiHP33N60E-E3  |
| Lead (Pb)-free and Halogen-free | SiHP33N60E-GE3 |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                                 | SYMBOL           | LIMIT                           | UNIT |
|-----------------------------------------------------------|------------------|---------------------------------|------|
| Drain-Source Voltage                                      | $V_{DS}$         | 600                             | V    |
| Gate-Source Voltage                                       | $V_{GS}$         | $\pm 30$                        |      |
| Continuous Drain Current ( $T_J = 150$ °C)                | $V_{GS}$ at 10 V | $T_C = 25$ °C                   | A    |
|                                                           |                  | $T_C = 100$ °C                  |      |
| Pulsed Drain Current <sup>a</sup>                         | $I_{DM}$         | 88                              |      |
| Linear Derating Factor                                    |                  | 2.2                             | W/°C |
| Single Pulse Avalanche Energy <sup>b</sup>                | $E_{AS}$         | 793                             | mJ   |
| Maximum Power Dissipation                                 | $P_D$            | 278                             | W    |
| Operating Junction and Storage Temperature Range          | $T_J, T_{stg}$   | -55 to +150                     | °C   |
| Drain-Source Voltage Slope                                | $dV/dt$          | $V_{DS} = 0$ V to 80 % $V_{DS}$ | V/ns |
| Reverse Diode $dV/dt$ <sup>d</sup>                        |                  |                                 |      |
| Soldering Recommendations (Peak temperature) <sup>c</sup> | for 10 s         | 300                             | °C   |

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 7.5$  A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100$  A/ $\mu$ s, starting  $T_J = 25$  °C.

**THERMAL RESISTANCE RATINGS**

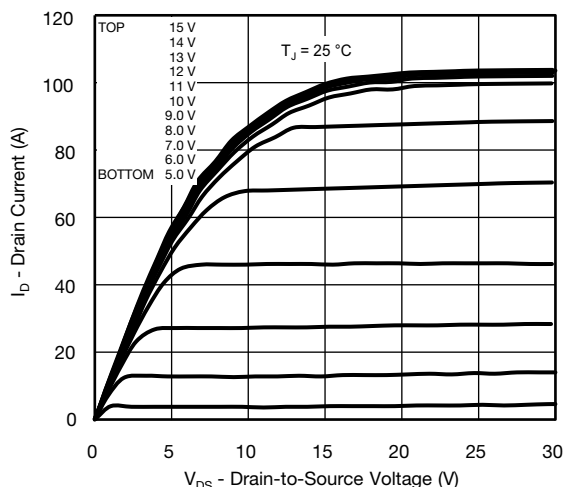
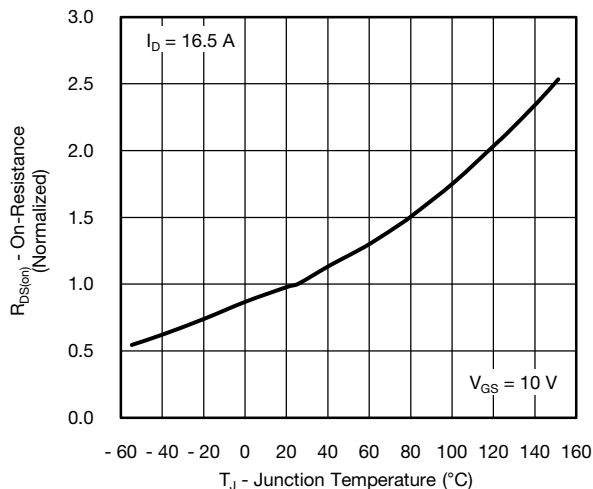
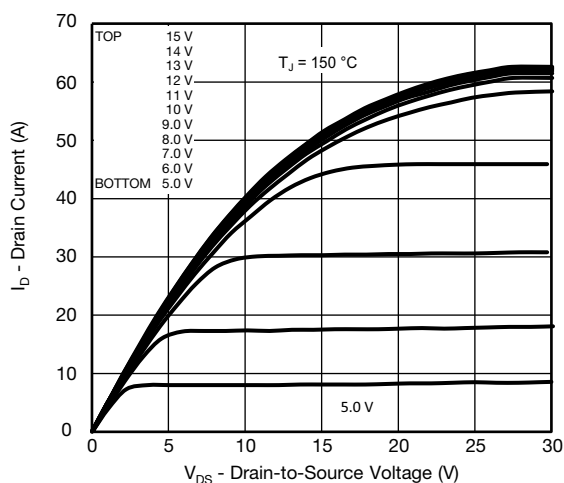
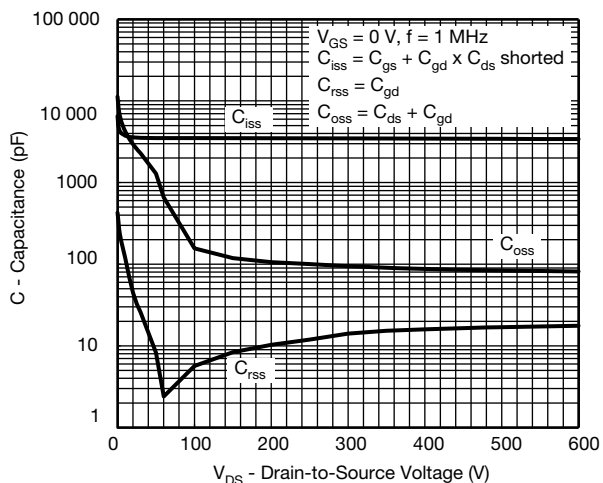
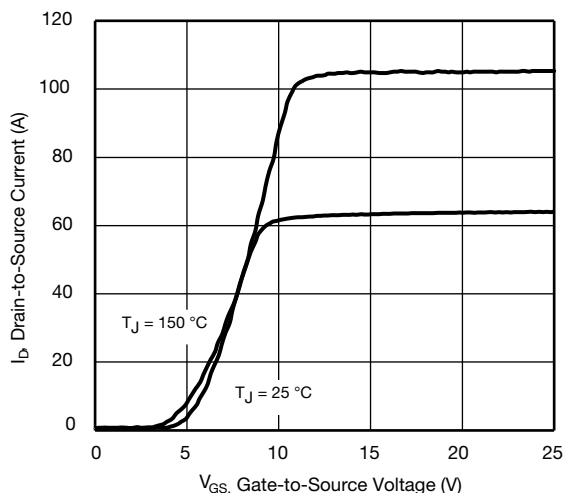
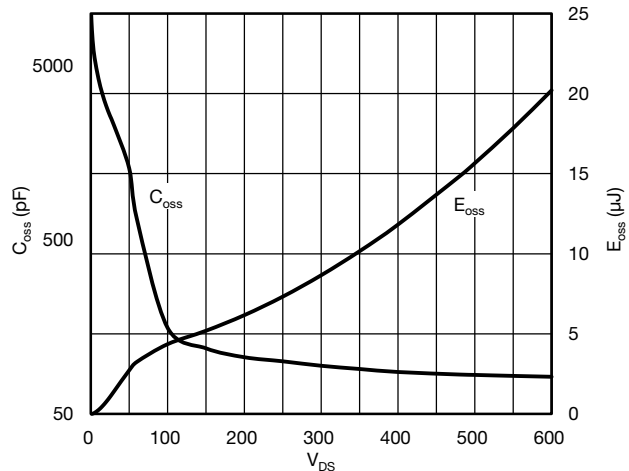
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 62   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 0.45 |      |

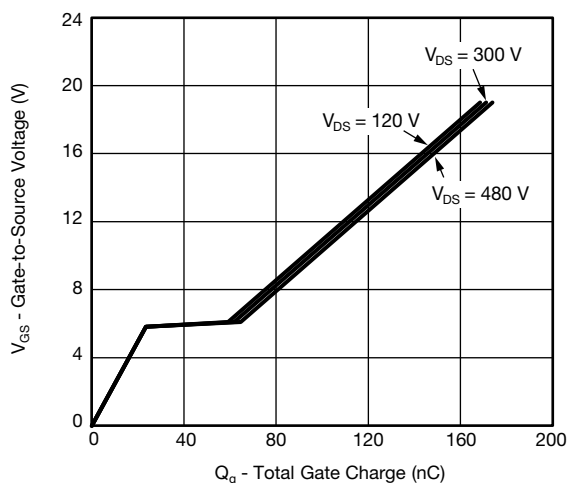
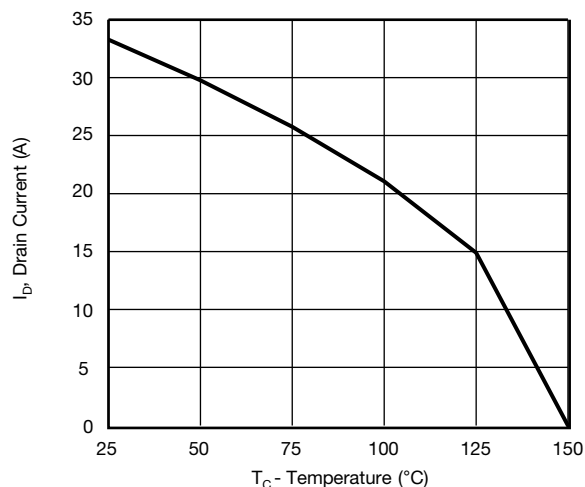
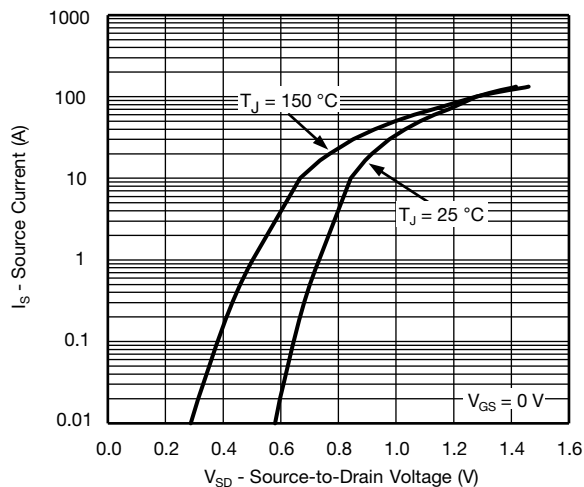
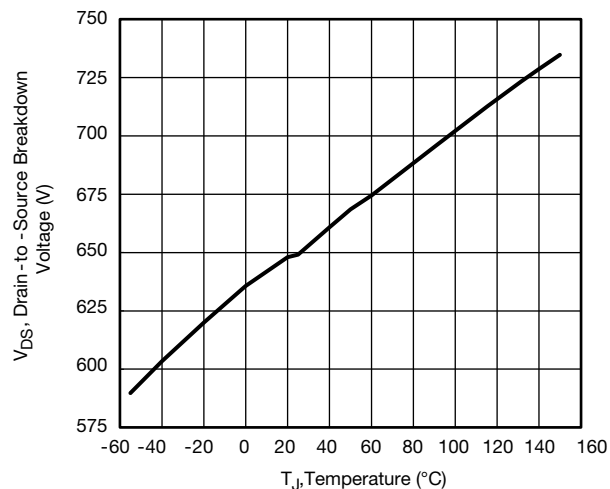
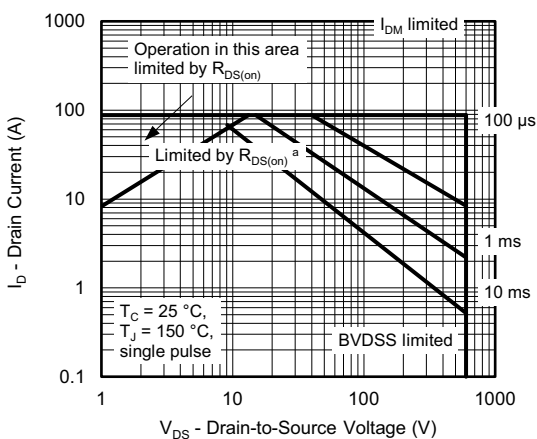
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

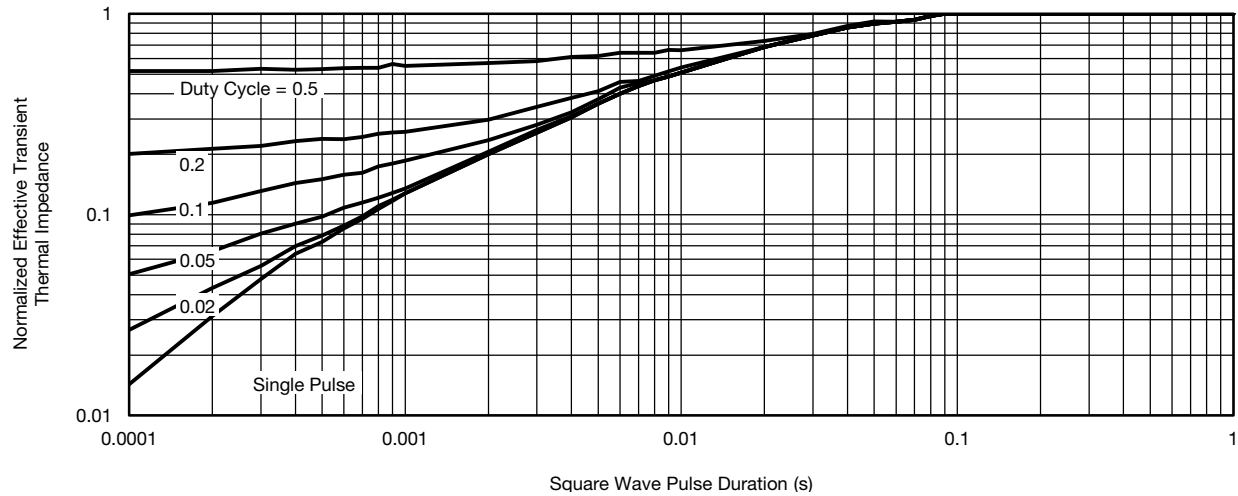
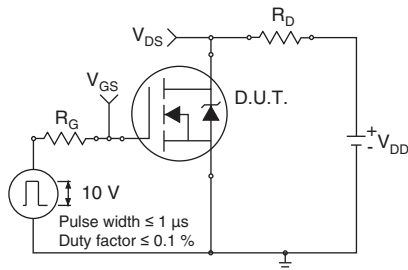
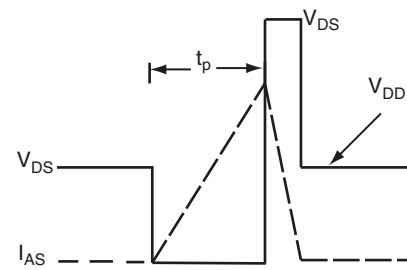
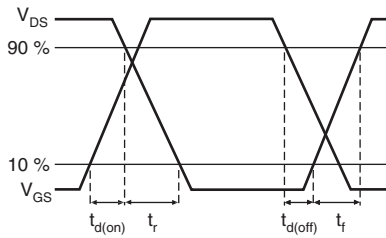
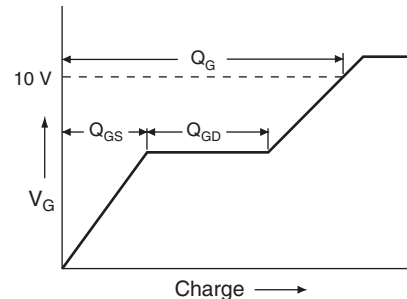
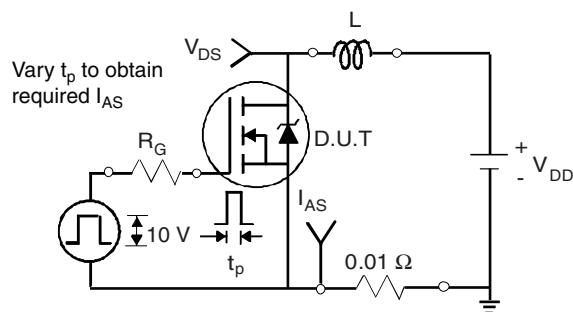
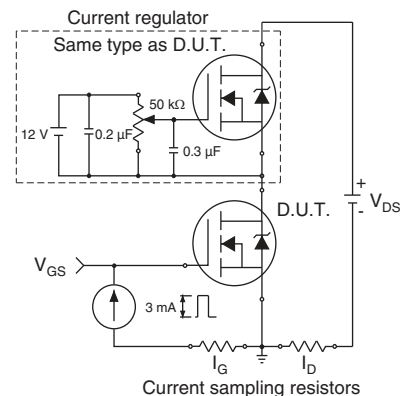
| PARAMETER                                                 | SYMBOL              | TEST CONDITIONS                                                                                                                                          | MIN. | TYP.  | MAX.      | UNIT                  |
|-----------------------------------------------------------|---------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------|------|-------|-----------|-----------------------|
| <b>Static</b>                                             |                     |                                                                                                                                                          |      |       |           |                       |
| Drain-Source Breakdown Voltage                            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                   | 600  | -     | -         | V                     |
| $V_{DS}$ Temperature Coefficient                          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 1\text{ mA}$                                                                                          | -    | 0.71  | -         | V/ $^{\circ}\text{C}$ |
| Gate-Source Threshold Voltage (N)                         | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                                                       | 2.0  | -     | 4.0       | V                     |
| Gate-Source Leakage                                       | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$                                                                                                                               | -    | -     | $\pm 100$ | nA                    |
|                                                           |                     | $V_{GS} = \pm 30\text{ V}$                                                                                                                               | -    | -     | $\pm 1$   | $\mu\text{A}$         |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$           | $V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                                          | -    | -     | 1         | $\mu\text{A}$         |
|                                                           |                     | $V_{DS} = 480\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^{\circ}\text{C}$                                                                    | -    | -     | 10        |                       |
| Drain-Source On-State Resistance                          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$ , $I_D = 16.5\text{ A}$                                                                                                           | -    | 0.083 | 0.099     | $\Omega$              |
| Forward Transconductance <sup>a</sup>                     | $g_{fs}$            | $V_{DS} = 30\text{ V}$ , $I_D = 16.5\text{ A}$                                                                                                           | -    | 11    | -         | S                     |
| <b>Dynamic</b>                                            |                     |                                                                                                                                                          |      |       |           |                       |
| Input Capacitance                                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 100\text{ V}$ ,<br>$f = 1\text{ MHz}$                                                                               | -    | 3508  | -         | pF                    |
| Output Capacitance                                        | $C_{oss}$           |                                                                                                                                                          | -    | 156   | -         |                       |
| Reverse Transfer Capacitance                              | $C_{rss}$           |                                                                                                                                                          | -    | 6     | -         |                       |
| Effective Output Capacitance, Energy Related <sup>b</sup> | $C_{o(er)}$         | $V_{GS} = 0\text{ V}$ , $V_{DS} = 0\text{ V to } 480\text{ V}$                                                                                           | -    | 136   | -         |                       |
| Effective Output Capacitance, Time Related <sup>c</sup>   | $C_{o(tr)}$         |                                                                                                                                                          | -    | 468   | -         |                       |
| Total Gate Charge                                         | $Q_g$               | $V_{GS} = 10\text{ V}$ , $I_D = 16.5\text{ A}$ , $V_{DS} = 480\text{ V}$                                                                                 | -    | 100   | 150       | nC                    |
| Gate-Source Charge                                        | $Q_{gs}$            |                                                                                                                                                          | -    | 24    | -         |                       |
| Gate-Drain Charge                                         | $Q_{gd}$            |                                                                                                                                                          | -    | 42    | -         |                       |
| Turn-On Delay Time                                        | $t_{d(on)}$         | $V_{DD} = 480\text{ V}$ , $I_D = 16.5\text{ A}$<br>$R_g = 9.1\text{ }\Omega$ , $V_{GS} = 10\text{ V}$                                                    | -    | 28    | 56        | ns                    |
| Rise Time                                                 | $t_r$               |                                                                                                                                                          | -    | 60    | 90        |                       |
| Turn-Off Delay Time                                       | $t_{d(off)}$        |                                                                                                                                                          | -    | 99    | 150       |                       |
| Fall Time                                                 | $t_f$               |                                                                                                                                                          | -    | 54    | 80        |                       |
| Gate Input Resistance                                     | $R_g$               | $f = 1\text{ MHz}$ , open drain                                                                                                                          | 0.2  | 0.7   | 1.0       | $\Omega$              |
| <b>Drain-Source Body Diode Characteristics</b>            |                     |                                                                                                                                                          |      |       |           |                       |
| Continuous Source-Drain Diode Current                     | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode<br> | -    | -     | 33        | A                     |
| Pulsed Diode Forward Current                              | $I_{SM}$            |                                                                                                                                                          | -    | -     | 88        |                       |
| Diode Forward Voltage                                     | $V_{SD}$            | $T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 16.5\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                       | -    | 0.9   | 1.2       | V                     |
| Reverse Recovery Time                                     | $t_{rr}$            | $T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = I_S$ ,<br>$dI/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 20\text{ V}$                                           | -    | 503   | 1006      | ns                    |
| Reverse Recovery Charge                                   | $Q_{rr}$            |                                                                                                                                                          | -    | 8.5   | 17        | $\mu\text{C}$         |
| Reverse Recovery Current                                  | $I_{RRM}$           |                                                                                                                                                          | -    | 26    | -         | A                     |

**Notes**

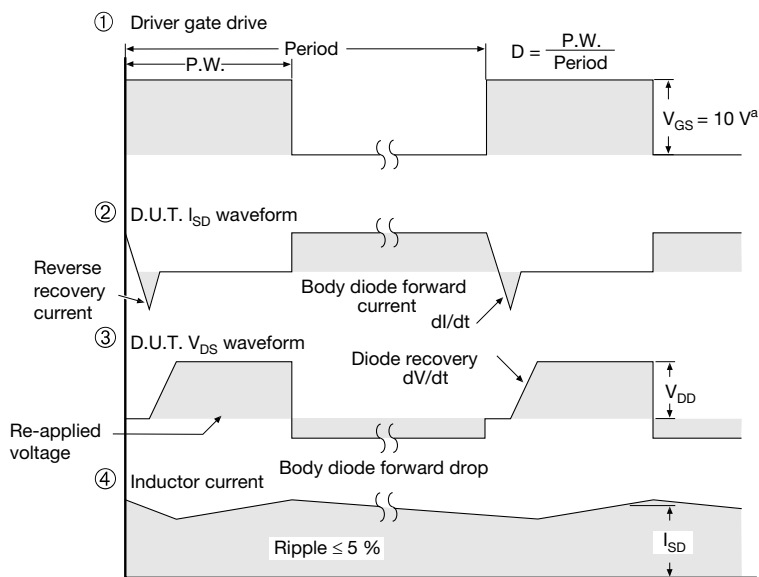
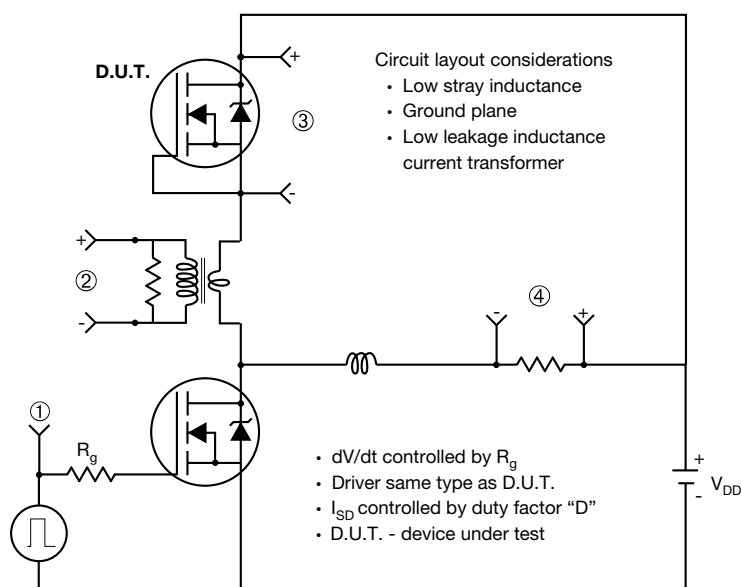
- a. Repetitive rating; pulse width limited by maximum junction temperature.  
b.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
c.  $C_{oss(tr)}$  is a fixed capacitance that gives the charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 10 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

**Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature**

**Fig. 9 - Maximum Safe Operating Area**


**Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case**

**Fig. 13 - Switching Time Test Circuit**

**Fig. 16 - Unclamped Inductive Waveforms**

**Fig. 14 - Switching Time Waveforms**

**Fig. 17 - Basic Gate Charge Waveform**

**Fig. 15 - Unclamped Inductive Test Circuit**

**Fig. 18 - Gate Charge Test Circuit**

### Peak Diode Recovery dV/dt Test Circuit



### Note

a.  $V_{GS} = 5 \text{ V}$  for logic level devices

**Fig. 19 - For N-Channel**

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